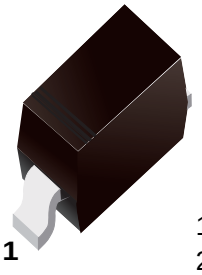
■ FEATURES

- Low Forward Voltage Drop.
- Guard Ring Construction For Transient Protection.
- Negligible Reverse Recovery Time.
- Low Reverse Capacitance.



1.Cathode
2.Anode

■ **Simplified outline(SOD-323)**

Top View

APPLICATIONS

- Schotty barrier switching.

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■ MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol	1N5819WS	1N5819BWS	1N5819CWS	Unit
Peak Repetitive Peak reverse voltage Working Peak DC Reverse Voltage	V_{RR} V_{RWM} V_R	40	30	20	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	21	14	V
Forward Continuous Current	I_F	350			mA
Repetitive Peak Forward Current @t≤1.0s	I_{FRM}	1.5			A
Power Dissipation	P_d	400			mW
Thermal Resistance Junction to Ambient	$R_{\theta jA}$	300			℃/W
Storage temperature	T_{stg}	-65~+125			℃

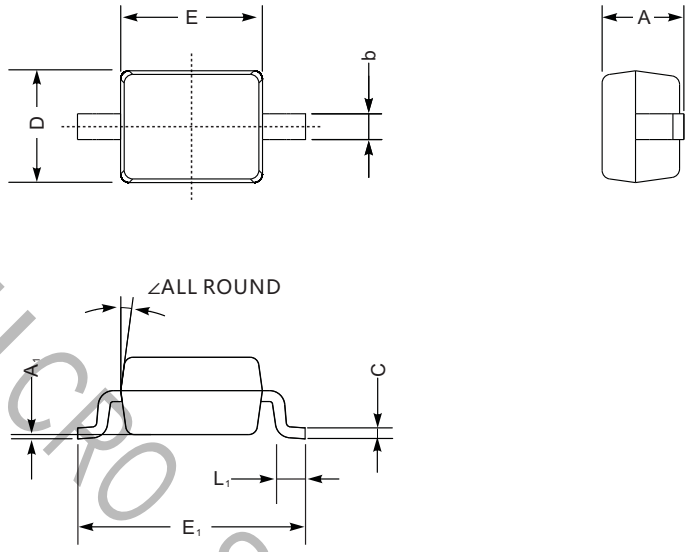
■ ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage 1N5819WS 1N5819BWS 1N5819CWS	$V_{(BR)R}$	40 30 20			V	I_R=10μA I_R=10μA I_R=10μA
Forward voltage	V_F			0.37 0.60	V	I_F=20mA I_F=200mA
Reverse current 1N5819WS 1N5819BWS 1N5819CWS	I_{RM}			5.0	μA	V_R=30V V_R=20V V_R=10V
Capacitance between terminals	C_T		50		pF	V_R=0,f=1MHz
Reverse Recovery Time	t_{rr}		10		ns	I_R=I_F=200mA I_{rr}=0.1*I_R,R_L=100Ω

■ Marking

NO.	1N5819WS	1N5819BWS	1N5819CWS
Marking	S4	S5	S6

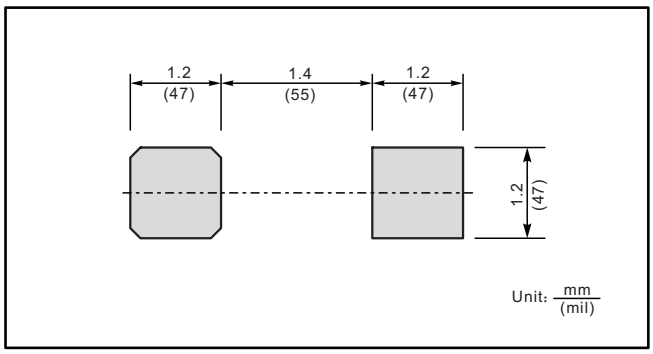
■ SOD-323



SOD-323 mechanical data

UNIT		A	C	D	E	E_1	b	L_1	A_1	∠
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2	9°
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—	
mil	max	43	5.9	55	70	108	16	16	8	
	min	32	3.1	47	63	100	9.8	7.9	—	

■ The recommended mounting pad size



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